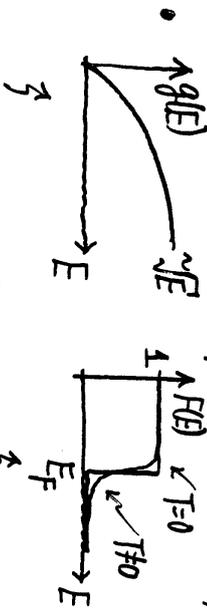


H. Electronic Contribution to heat capacity

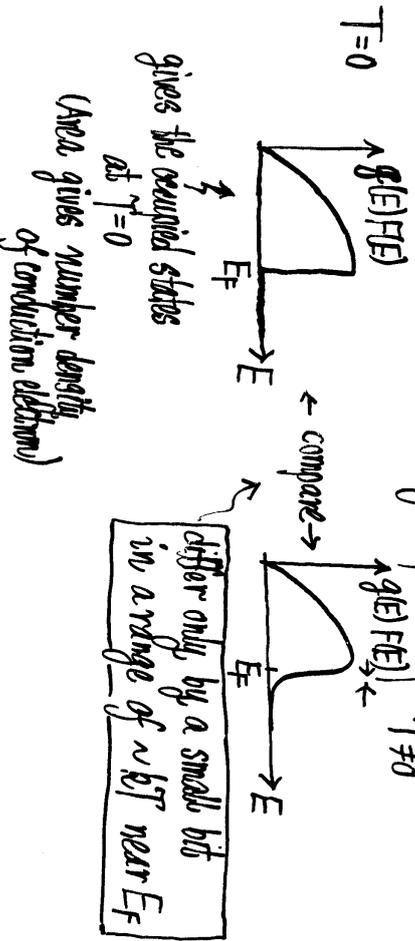
- Recall: Phonon contribution $\sim T^3$ (Debye)
- For conductors, there is a $\sim T$ (linear T) part that shows up clearly in low-temperature data (see figure)

Qualitative understanding of $\sim T$ terms: on next page)

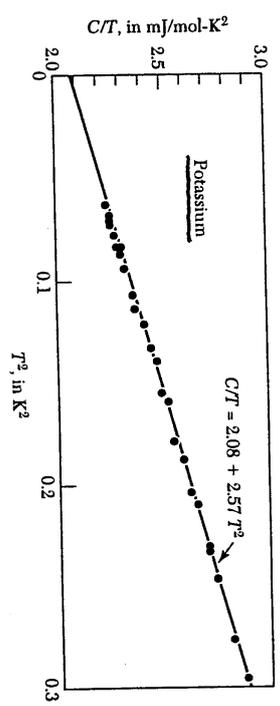
- $T=0$, all states up to E_F are occupied



(no information on occupancy of states)



Experimental Facts



Experimental results of Potassium at very low temperatures

$\frac{C}{T} \propto T^2$ gives a straight line (metals)

$\Rightarrow C = \gamma T + \alpha T^3$

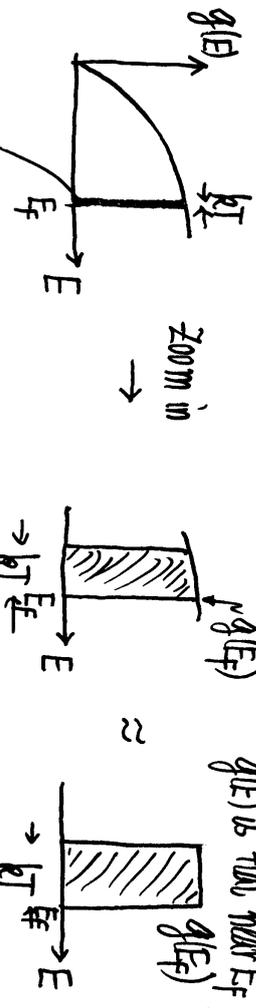
- this term appears in metals only
- it is apparent only at very low temperatures
- comes from the electrons (ideal Fermi gas) at $T \ll T_F$
- due to lattice vibrations (phonons)
- this term appears in both metals and insulators
- this term becomes smaller at low temperatures because kT cannot excite most of the normal modes (oscillators)

$C = \frac{\partial U}{\partial T}$

$U(T) - U(T=0) = \text{change in energy due to electrons near } E_F$

$\approx (g(E_F) kT) \cdot kT$

$kT \sim 0.01 \text{ eV}$, $E_F \sim \text{a few eV}$ ($kT \ll E_F$)



These electrons may be affected by temperature, as there are unoccupied states in their vicinity

Area = $g(E_F) \cdot kT$
= # electrons affected by thermal energy kT

$\therefore C \approx 2 g(E_F) k^2 T \sim T$ (as observed)

A full calculation (statistical physics) gives

$C = \frac{\pi^2}{3} g(E_F) k^2 T$

\therefore Hand-waving argument gives very good result!

[since it captures the key physics - Pauli Exclusion Principle]

\therefore Measuring $C \Rightarrow \gamma$ (metals)

$\Rightarrow g(E_F)$ (DOS at E_F)

What if we don't know QM and Pauli Exclusion Principle?

"Free electrons" $\Rightarrow \frac{p_x^2}{2m} + \frac{p_y^2}{2m} + \frac{p_z^2}{2m}$

for each particle

Classical statistical mechanics $\Rightarrow \frac{1}{2} kT$ for each term

$\therefore U = N \cdot 3 \cdot \frac{1}{2} kT$

$\Rightarrow C_{\text{classical}} = \frac{3}{2} Nk$ (wrong!)

This should be compared with

$C = \frac{\pi^2}{3} g(E_F) k^2 T$
 $= \frac{\pi^2}{2} Nk \cdot \left(\frac{kT}{E_F}\right)$

$\sim C_{\text{classical}} \cdot \left(\frac{kT}{E_F}\right)$

$\ll 1$ ($\sim 10^{-2}$)

$\therefore C_{\text{actual}} \ll C_{\text{classical}}$

(since most electrons can't contribute due to Pauli Exclusion Principle)

I. A review on basis of (one quantum) transport theory.

(a) R, ρ, σ, α (Resistance, conductance, resistivity, conductivity)

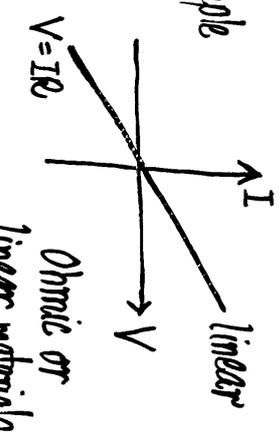
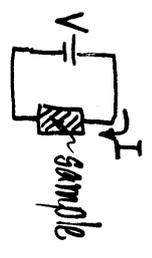
$R = \frac{V}{I}$ ← Voltage across a piece of material (Volts)
 ← current (Amperes)
 resistance (Ohm)

the equation defines R - depends on material and dimensions (size)

$G = \frac{1}{R}$ defines G and dimensions (size)
 ← conductance of sample

Ohm's law:

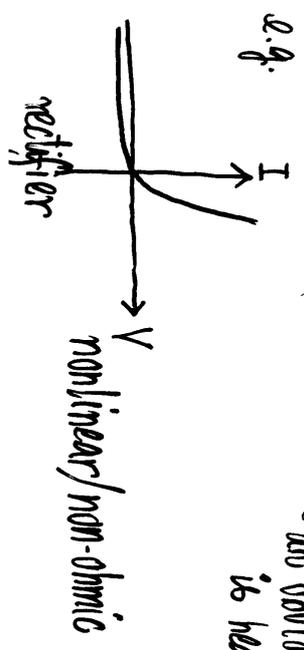
$R = \text{constant}$



Note: Many (useful) materials show non-ohmic I-V.

I(V) such that $\frac{V}{I} \neq \text{constant}$

an obvious / simple reason is heating / temperature effect



$R = \rho \frac{L}{A}$
 resistivity (a material's property) (Ohm-m)

$\vec{J} = \sigma \vec{E}$
 ← current density
 ← electric field
 conductivity = $\frac{1}{\rho}$ [units: (Ohm-m)⁻¹ or $\frac{S}{m}$]

Ohmic (linear) materials:

σ is independent of \vec{E}

Isotropic materials: (各向同性)

$\vec{J} = \sigma \vec{E}$ a scalar quantity, \vec{J} follows the direction of \vec{E}

Anisotropic materials:

$\vec{J} = \hat{\sigma} \vec{E}$
 ← tensor (3x3 matrix)

$$\begin{pmatrix} J_x \\ J_y \\ J_z \end{pmatrix} = \begin{pmatrix} \sigma_{xx} & \sigma_{xy} & \sigma_{xz} \\ \sigma_{yx} & \sigma_{yy} & \sigma_{yz} \\ \sigma_{zx} & \sigma_{zy} & \sigma_{zz} \end{pmatrix} \begin{pmatrix} E_x \\ E_y \\ E_z \end{pmatrix}$$

- Real materials show a very wide range of ρ or σ
- can differ by $\sim 10^{24}$!

$10^8 \Omega\text{-m}$

good conductors

Electrical Resistivity (ohm-m)	(log)	Electrical Conductivity (S/m)
-8	8	
-7	7	copper, silver, iron
-6	6	stainless steel, metallic glass
-5	5	YBa ₂ Cu ₃ O ₇ (ab plane)
-4	4	YBa ₂ Cu ₃ O ₇ (c-axis)
-3	3	silicon (doped)
-2	2	ZnO (doped) seawater
-1	1	Fe ₃ O ₄
0	0	germanium
1	-1	
2	-2	silicon
3	-3	InSb
4	-4	
5	-5	water
6	-6	AgCl
7	-7	
8	-8	ZnO (undoped)

10^8 S/m ($10^8 \Omega\text{-m}^{-1}$)

steel: alloyed iron

high Tc SC
Laminar (superconductor)

semiconductors

insulators
 $10^{16} \Omega\text{-m}$

10^{-16} S/m

Resistivity and conductivity of a variety of materials at room temperature. (Note: values are approximate, and for insulators and semiconductors, very sensitive to impurities.)

Z	Element	$\rho(\Omega\text{ m})$	$\sigma(\text{S m}^{-1})$	Z	Element	$\rho(\Omega\text{ m})$	$\sigma(\text{S m}^{-1})$
1	Hydrogen, H	—	—	49	Indium, In	8.37×10^{-4}	1.19×10^7
2	Helium, He	—	—	50	Tin, Sn	1.1×10^{-2}	9.1×10^6
3	Lithium, Li	8.55×10^{-4}	1.17×10^7	51	Antimony, Sb	3.9×10^{-2}	2.56×10^6
4	Beryllium, Be	4×10^{-4}	2.5×10^7	52	Tellurium, Te	0.00436	229
5	Boron, B	18000	5.56×10^{-4}	53	Iodine, I	1.37×10^{-2}	7.30×10^6
6	Carbon (diamond), C	10 ¹¹	10^{-11}	54	Xenon, Xe	—	—
7	Nitrogen, N	—	—	55	Caesium, Cs	2×10^{-2}	5×10^6
8	Oxygen, O	—	—	56	Barium, Ba	5×10^{-2}	2×10^6
9	Fluorine, F	—	—	57	Lanthanum, La	5.7×10^{-2}	1.75×10^6
10	Neon, Ne	—	—	58	Cerium, Ce	7.3×10^{-2}	1.37×10^6
11	Sodium, Na	4.2×10^{-4}	2.38×10^7	59	Praseodymium, Pr	6.8×10^{-2}	1.47×10^6
12	Magnesium, Mg	4.38×10^{-4}	2.28×10^7	60	Neodymium, Nd	6.4×10^{-2}	1.56×10^6
13	Aluminium, Al	2.66×10^{-4}	3.77×10^7	61	Promethium, Pm	5×10^{-2}	2×10^6
14	Silicon, Si	0.001	1000	62	Samarium, Sm	9.4×10^{-2}	1.06×10^6
15	Phosphorus, P	1×10^{15}	1×10^{-15}	63	Europium, Eu	9×10^{-2}	1.11×10^6
16	Sulphur, S	2×10^{15}	5×10^{-16}	64	Gadolinium, Gd	1.34×10^{-1}	7.46×10^5
17	Chlorine, Cl	—	—	65	Terbium, Tb	1.14×10^{-1}	8.77×10^5
18	Argon, Ar	—	—	66	Dysprosium, Dy	5.7×10^{-1}	1.75×10^5
19	Potassium, K	6.15×10^{-4}	1.63×10^7	67	Holmium, Ho	8.7×10^{-1}	1.15×10^5
20	Calcium, Ca	3.43×10^{-4}	2.92×10^7	68	Erbium, Er	8.7×10^{-1}	1.15×10^5
21	Scandium, Sc	6.1×10^{-2}	1.64×10^6	69	Thulium, Th	7.9×10^{-1}	1.27×10^5
22	Titanium, Ti	4.2×10^{-2}	2.38×10^6	70	Ytterbium, Yb	2.9×10^{-1}	3.45×10^5
23	Vanadium, V	2.48×10^{-2}	4.03×10^6	71	Lutetium, Lu	7.9×10^{-1}	1.27×10^5
24	Chromium, Cr	1.27×10^{-2}	7.87×10^6	72	Hafrnium, Hf	3.51×10^{-1}	2.85×10^5
25	Manganese, Mn	1.85×10^{-4}	5.41×10^5	73	Tantalum, Ta	1.25×10^{-1}	8.03×10^5
26	Iron, Fe	9.71×10^{-4}	1.03×10^7	74	Tungsten, W	5.65×10^{-4}	1.77×10^7
27	Cobalt, Co	6.24×10^{-4}	1.60×10^7	75	Rhenium, Re	1.93×10^{-2}	5.18×10^6
28	Nickel, Ni	6.84×10^{-4}	1.46×10^7	76	Osmium, Os	8.12×10^{-2}	1.23×10^7
29	Copper, Cu	1.67×10^{-4}	5.98×10^7	77	Iridium, Ir	5.3×10^{-2}	1.89×10^7
30	Zinc, Zn	5.92×10^{-4}	1.69×10^7	78	Platinum, Pt	1.06×10^{-1}	9.43×10^6
31	Gallium, Ga	2.7×10^{-2}	3.70×10^6	79	Gold, Au	2.35×10^{-4}	4.28×10^7
32	Germanium, Ge	0.46	2.1739	80	Mercury, Hg	9.41×10^{-2}	1.06×10^6
33	Arsenic, As	2.6×10^{-2}	3.85×10^6	81	Thallium, Th	1.8×10^{-2}	5.56×10^6
34	Selenium, Se	0.01	100	82	Lead, Pb	2.07×10^{-2}	4.84×10^6
35	Bromine, Br	—	—	83	Bismuth, Bi	1.068×10^{-1}	9.36×10^5
36	Krypton, Kr	—	—	84	Polonium, Po	1.4×10^{-4}	7.14×10^5
37	Rubidium, Rb	1.25×10^{-2}	8×10^6	85	Astatine, At	—	—
38	Strontium, Sr	2.3×10^{-2}	4.35×10^6	86	Radon, Rn	—	—
39	Yttrium, Y	5.7×10^{-2}	1.75×10^6	87	Francium, Fr	—	—
40	Zirconium, Zr	4.21×10^{-2}	2.37×10^6	88	Radium, Ra	1×10^{-4}	1×10^6
41	Niobium, Nb	1.25×10^{-2}	8×10^6	89	Actinium, Ac	—	—
42	Molybdenum, Mo	5.2×10^{-2}	1.92×10^7	90	Thorium, Th	1.3×10^{-2}	7.69×10^6
43	Ruthenium, Ru	2.26×10^{-2}	4.42×10^6	91	Protactinium, Pa	1.77×10^{-2}	5.65×10^6
44	Rhenium, Re	7.6×10^{-2}	1.32×10^7	92	Uranium, U	3.06×10^{-2}	3.25×10^6
45	Rhodium, Rh	4.51×10^{-4}	2.22×10^7	93	Neptunium, Np	1.22×10^{-4}	8.20×10^5
46	Palladium, Pd	1.08×10^{-2}	9.26×10^6	94	Plutonium, Pu	1.46×10^{-4}	6.85×10^5
47	Silver, Ag	1.59×10^{-4}	6.29×10^7	95	Americium, Am	6.8×10^{-7}	1.4706×10^6
48	Cadmium, Cd	6.83×10^{-4}	1.46×10^7				

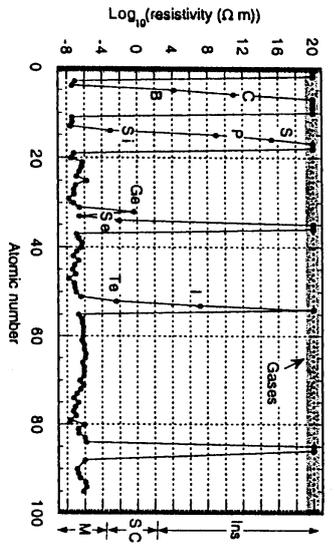
ρ and σ of pure elements at room temperature

From J.D. Livingston, "Electronic Properties of Engineering Materials"

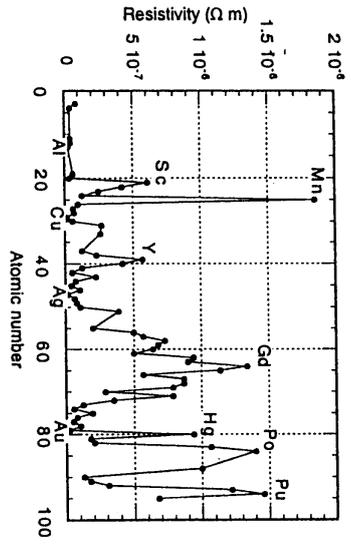
- Most are conductors (elemental solids)
- Only a few are exceptional bad conductors, e.g. C, S, Si, Ge, Se.

elements at room temperature

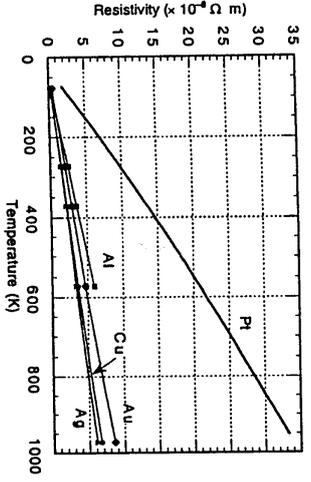
VII-37



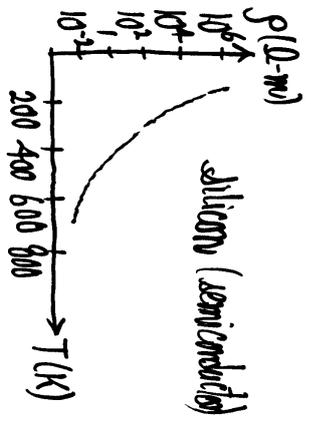
Insulators
Semiconductors
metals



zoom in
linear scale



$\rho(T)$ for metals



silicon (semiconductor)

VII-38

Q: $\rho(T)$ for metals? for semiconductors?

Q: Why do we have materials with ρ or σ differ by 10^{24} ?

To answer these questions, we need to involve ideas in quantum mechanics

(b) Drude model of σ (~1900)

without knowing QM

classical free-electron theory of metals
good conductors
[models conductors for theory: Na, K]

use non-quantum physics
discovered in 1897 by Thomson

interactions between e^- and e^- and e^- with ions are neglected
between collisions

Metal: ions + sea of free electrons



Drude: This sea of electrons is responsible for conduction.

Drude:

Do the electrons move around for $\vec{E} = 0$? (without applied field)
 Yes, thermal motion

→ but electrons move around in all directions
 (no preferred direction)

⇒ No net charge through a unit area per unit time
 ⇒ $\vec{J} = 0$

□ An estimate of $v_{thermal}$: (classical theory)

$$\frac{1}{2} m v_{th}^2 = \frac{3}{2} kT \Rightarrow v_{th} = \sqrt{\frac{3kT}{m}}$$

For $T \sim 300K$,
 $v_{th} \sim 10^5 \text{ ms}^{-1}$
 \approx mass of e^-

high speed

How about $\vec{E} \neq 0$? (with applied field)

• We know $\vec{E} \neq 0$, $\vec{J} \neq 0$

⇒ \vec{E} gives an average drift velocity, \vec{v}_d to the electrons
 ($v_d \ll v_{th}$)

In terms of \vec{v}_d ,

$$\vec{J} = -e n v_d$$

(1)



charges in this volume $A v_d \cdot A t$ will pass through a cross section A in time $A t$ due to average drift velocity v_d

charges in volume $A v_d \cdot A t = (-e) n \cdot A v_d \cdot A t$

$$J = \frac{\# \text{ charges}}{\text{area} \cdot \text{time}}$$

$$\vec{J} = \frac{(-e) n \cdot A \cdot \vec{v}_d \cdot A t}{A \cdot A t} = -e n \vec{v}_d$$

$\vec{E} \neq 0$ gives $\vec{v}_d \neq 0$ and hence $\vec{J} \neq 0$

A related quantity is mobility, μ_e .

in semiconductor handbooks, one can find data on mobility.

Mobility μ_e :

Ohm's Law: σ is field independent ($\vec{J} = \sigma \vec{E}$)

$$\vec{J} = -en\vec{v}_D$$

The two equations are consistent if $\vec{v}_D \propto \vec{E}$

$$\vec{J} = -en\vec{v}_D$$

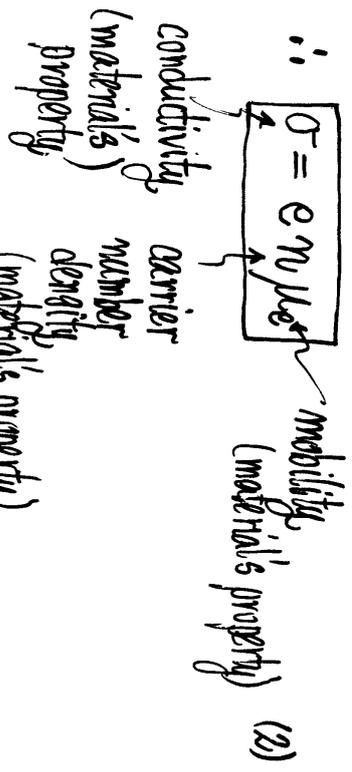
$$= -en\mu_e(-\mu_e \vec{E})$$

$$= en\mu_e \vec{E}$$

$$= \sigma \vec{E}$$

write as $\vec{v}_D = -\mu_e \vec{E}$

due to (-e) charge of electrons
mobility [units: $m^2 V^{-1} s^{-1}$]



RHS: isolate the 2 factors affecting σ

Remarks: (1) and (2) are general relations.

Effect of $\vec{E} \neq 0$

• leads to \vec{v}_D

• but \vec{J} does not keep on increasing with time!

\Rightarrow the simple idea of \vec{E} -field accelerates the electrons:

$$m \frac{d\vec{v}}{dt} = -e\vec{E} \Rightarrow \vec{v} = \frac{-e}{m} \vec{E} t$$

$$\Rightarrow \vec{J} \propto t$$

does NOT work!

• Experimentally, after the circuit is closed, the ammeter reading increases and then eventually becomes stationary.

Analogy: (a) Why ain't you hurt when raindrops keep falling on your head?

(b) Millikan's oil drop experiment

Idea: Terminal Velocity!

How can the electrons attain a terminal velocity in the presence of \vec{E} ?

Needs a frictional or damping term

Source: come from electrons' frequent collisions with ions

Equation of motion / Hydrodynamic description of frictional force (drag) due to collisions

• Collisions serve as a source of frictional or viscous drag forces

Viscous force: \square oppose motion $\square \propto v$

Eq. of motion:

$$m \frac{d\vec{v}_D}{dt} = \vec{F} = \underbrace{-e\vec{E}}_{\substack{\text{sum of} \\ \text{all forces}}} - \underbrace{\frac{m\vec{v}_D}{\tau}}_{\substack{\text{driving} \\ \text{force}}} + \underbrace{\text{other possible forces}}_{\substack{\text{frictional drag} \\ \text{due to collisions}}}$$

$$\therefore \boxed{m \frac{d\vec{v}_D}{dt} \approx -\frac{m\vec{v}_D}{\tau} - e\vec{E}} \quad (*)$$

τ = a parameter characterizes the importance of collisions

\approx average time between collisions
= collision time or relaxation time

Noting $\vec{p} = m\vec{v}_D = m\vec{v}_D$

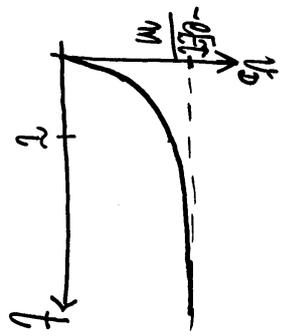
$$\frac{d\vec{p}}{dt} = -\frac{\vec{p}}{\tau} - e\vec{E}$$

+ Thus, the Drude model amounts to saying that the electrons are accelerated by the E-field only for the duration τ between collisions.

(*) can be solved to give:

$$\vec{v}_D = \frac{-eE\tau}{m} [1 - e^{-t/\tau}]$$

For $t \gg \tau$, \vec{v}_D becomes saturated (terminal velocity)



\swarrow steady state

In steady state, $\frac{d\vec{v}_D}{dt} = 0 \Rightarrow -\frac{m\vec{v}_D}{\tau} = e\vec{E}$

$$\Rightarrow \vec{v}_D = -\frac{e\tau}{m} \vec{E}$$

$\mu_D = \text{mobility}$

\therefore Collisions \rightarrow frictional drag \rightarrow a steady \vec{v}_D

$$\vec{J} = -en\vec{v}_D = \frac{ne^2\tau}{m} \vec{E} = \sigma \vec{E}$$

$$\therefore \boxed{\sigma = \frac{ne^2\tau}{m}} \quad \text{key result}^+$$

Note: The condition $t \gg \tau$ means that there are many collisions in the time duration t .

+ Some of Drude's thoughts on what are causing τ is wrong. But the result $\sigma = \frac{ne^2\tau}{m}$ remains valid in quantum treatments.

$\vec{v}_D = -\frac{e\tau}{m} \vec{E}$ (not increasing with time, just like the terminal velocity)

$m\vec{v}_D = -e\tau \vec{E}$

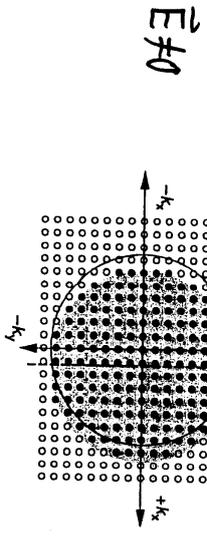
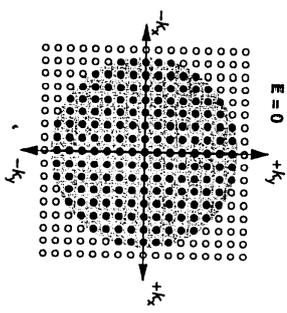
each electron acquires such momentum

$\underbrace{m\vec{v}_D}_{\vec{k}} = \frac{-e\tau \vec{E}}{\hbar}$

each electron shifts by this amount $\Delta \vec{k}$ in \vec{k} -space

$\vec{E} = 0$ Fermi sphere centered at $\vec{k} = 0$

$\vec{E} \neq 0$ shifted Fermi sphere



- shifted Fermi sphere in steady state
- steady state is maintained by \vec{E} and electron scattering processes

$\sigma = \frac{ne^2\tau}{m}$

- The most important formula in thinking about conductivity
- τ or $1/\tau$ is a parameter that models the effects of scatterings of electrons that lead to resistance

▪ this parameter is not easy to calculate (needs SM perturbation theory)

▪ usually, this parameter can be extracted from data

• What kinds of scattering mechanism that would lead to resistance?

- electron - regular array of ions? X
- electron - lattice vibrations (electron-phonon scattering) ✓
- electron - impurity scattering ✓
- electron - sample boundary scattering ✓
- electron - electron scattering (Coulomb) ✓
- ⋮

Values of n for metals

VIII-47

VIII-48

FREE ELECTRON DENSITIES OF SELECTED METALLIC ELEMENTS*

ELEMENT	Z	n ($10^{22}/\text{cm}^3$)	r_s (Å)	r_s/a_0
Li (78 K)	1	4.70	1.72	3.25
Na (5 K)	1	2.65	2.08	3.93
K (5 K)	1	1.40	2.57	4.86
Rb (5 K)	1	1.15	2.75	5.20
Cs (5 K)	1	0.91	2.98	5.62
Cu	1	8.47	1.41	2.67
Ag	1	5.86	1.60	3.02
Au	1	5.90	1.59	3.01
Be	2	24.7	0.99	1.87
Mg	2	8.61	1.41	2.66
Ca	2	4.61	1.73	3.27
Sr	2	3.55	1.89	3.57
Ba	2	3.15	1.96	3.71
Nb	1	5.56	1.63	3.07
Fe	2	17.0	1.12	2.12
Mn (α)	2	16.5	1.13	2.14
Zn	2	2.30	2.30	2.30
Cd	2	13.2	1.22	2.59
Hg (78 K)	2	9.27	1.37	2.59
Al	3	8.65	1.40	2.65
Ga	3	18.1	1.10	2.07
In	3	15.4	1.16	2.19
Tl	3	11.5	1.27	2.41
Sn	4	10.5	1.31	2.48
Pb	4	14.8	1.17	2.22
Bi	5	13.2	1.22	2.30
Sb	5	14.1	1.19	2.25
		16.5	1.13	2.14

* At room temperature (about 300 K) and atmospheric pressure, unless otherwise noted. The radius r_s of the free electron sphere is defined in Eq. (1.2). We have arbitrarily selected one value of Z for those elements that display more than one chemical valence. The Drude model gives no theoretical basis for the choice. Values of n are based on data from R. W. G. Wyckoff, *Crystal Structures*, 2nd ed., Interscience, New York, 1963.

Note:

$$n \sim 10^{22} - 10^{23} / \text{cm}^3$$

From Ashcroft and Mermin: Solid State Physics

Q: How can one obtain n from crystal structure?
 from density? from atomic volume (cm^3/mole)?

Remarks: It is important to have some common sense on materials properties in studying solid state physics.

$\rho = \text{resistivity}$

$[\mu\Omega\text{-cm}]$

ELECTRICAL RESISTIVITIES OF SELECTED ELEMENTS*

ELEMENT	77 K	273 K	373 K	$\frac{\rho(77\text{K})}{\rho(273\text{K})}$	$\frac{\rho(77\text{K})}{\rho(373\text{K})}$
Li	1.04	8.55	12.4	1.06	
Na	0.8	4.2	Melted		
K	1.38	6.1	Melted		
Rb	2.2	11.0	Melted		
Cs	4.5	18.8	Melted		
Cu	0.2	1.56	2.24	1.05	
Ag	0.3	1.51	2.13	1.03	
Au	0.5	2.04	2.84	1.02	
Be		2.8	5.3	1.39	
Mg	0.62	3.9	5.6	1.05	
Ca		3.43	5.0	1.07	
Sr	7	23			
Ba	17	60			
Nb	3.0	15.2	19.2	0.92	
Fe	0.66	8.9	14.7	1.21	
Zn	1.1	5.5	7.8	1.04	
Cd	1.6	6.8			
Hg	5.8	Melted			
Al	0.3	2.45	Melted	1.06	
Ga	2.75	13.6	Melted		
In	1.8	8.0	12.1	1.11	
Tl	3.7	15	22.8	1.11	
Sn	2.1	10.6	15.8	1.09	
Pb	4.7	19.0	27.0	1.04	
Bi	35	107	156	1.07	
Sb	8	39	59	1.11	

* Resistivities in microhm centimeters are given at 77 K (the boiling point of liquid nitrogen at atmospheric pressure), 273 K, and 373 K. The last column gives the ratio of ρ/T at 373 K and 273 K to display the approximate linear temperature dependence of the resistivity near room temperature. Source: G. W. C. Kaye and T. H. Laby, *Table of Physical and Chemical Constants*, Longmans Green, London, 1966.

From Ashcroft and Mermin: Solid State Physics

$$\sigma = \frac{n e^2 \tau}{m} \Rightarrow \tau = \frac{m \sigma}{n e^2} = \frac{m}{n e^2 \rho}$$

[10⁻¹⁴s]

DRUDE RELAXATION TIMES IN UNITS OF 10⁻¹⁴ SECOND*

ELEMENT	77 K	273 K	373 K
Li	7.3	0.88	0.61
Na	17	3.2	
K	18	4.1	
Rb	14	2.8	
Cs	8.6	2.1	
Cu	21	2.7	1.9
Ag	20	4.0	2.8
Au	12	3.0	2.1
Be		0.51	0.27
Mg	6.7	1.1	0.74
Ca		2.2	1.5
Sr	1.4	0.44	
Ba	0.66	0.19	
Nb	2.1	0.42	0.33
Fe	3.2	0.24	0.14
Zn	2.4	0.49	0.34
Cd	2.4	0.56	
Hg	0.71		
Al	6.5	0.80	0.55
Ga	0.84	0.17	
In	1.7	0.38	0.25
Tl	0.91	0.22	0.15
Sn	1.1	0.23	0.15
Pb	0.57	0.14	0.099
Bi	0.072	0.023	0.016
Sb	0.27	0.055	0.036

Ex: Obtain τ from data of ρ and n

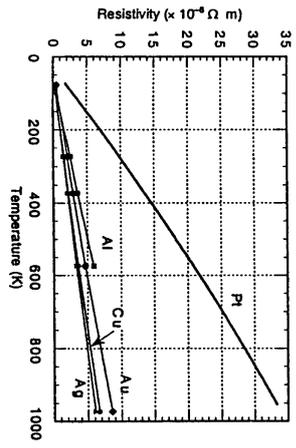
Ex: obtain the mobility, μ_e from data

Take Ag at 79K $\tau \sim 2 \times 10^{-14}$ s

$\lambda \sim$ mean free path $\sim v_F \cdot \tau \sim 10^5 \text{ms}^{-1} \cdot 10^{-13}\text{s} \sim 10^{-8}\text{m}$

Lattice constant $\sim 3\text{\AA} = 3 \times 10^{-10}\text{m}$

\Rightarrow electron can move through many lattice constants between scatterings!
Why? (need energy band theory)



$\rho(T)$ for good metals increase linearly with T in a range of temperature near and above room temp.

Why? Electron-phonon scatterings dominate
lattice vibrations

$$\sigma = \frac{n e^2 \tau}{m} \Rightarrow \rho = \frac{m}{n e^2} \cdot \frac{1}{\tau}$$

$\frac{1}{\tau}$ = "scattering rate" = # scatterings per second

$\frac{1}{\tau} \propto n_{ph}(T)$ = # phonons at temp. T

For $T \gg \theta_D$ (Debye temperature), $n_{ph}(T) \sim T$

$\therefore \frac{1}{\tau} \propto T \Rightarrow \rho \propto T$ (as observed)

Refs: Kittel Ch.6
Ashcroft and Mermin Ch.4